Silicon NPN Power Transistors 2SC1579

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		15	A
I_{CM}	Collector current-Peak		30	A
P_T	Total power dissipation	T_C=25℃	150	W
T_j	Junction temperature		200	℃
T_{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance from junction to mounting base	1.0	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ; I_B=0	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=10A; I_B=2A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=10A; I_B=2A			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=500V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=5A ; V_{CE}=4V	10		25	
f_T	Transition frequency	I_C=0.5A ; V_{CE}=10V		5		MHz

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PACKAGE OUTLINE

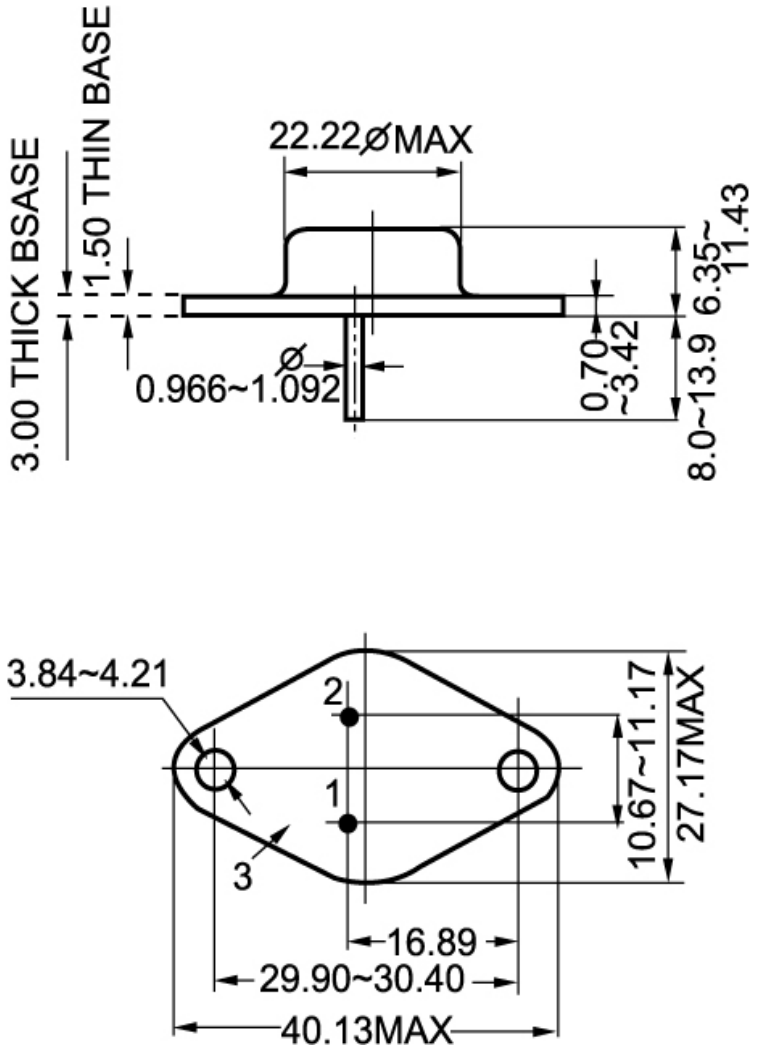

Fig.2 Outline dimensions